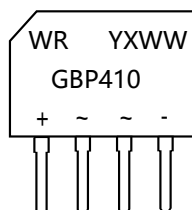


Ultrasoft Recovery Bridge



Features

- Glass Passivated Chip Junction
- Reverse Voltage - 1000 V
- Forward Current - 4A
- High Surge Current Capability
- Designed For Surface Mount Application

PINNING

PIN	DESCRIPTION
1	Input Pin (~)
2	Input Pin (~)
3	Output Anode (+)
4	Output Cathode (-)

Benefits

- Case: GBP
- Terminals: Solderable Per MIL-STD-750

Maximum Ratings and Electrical characteristics

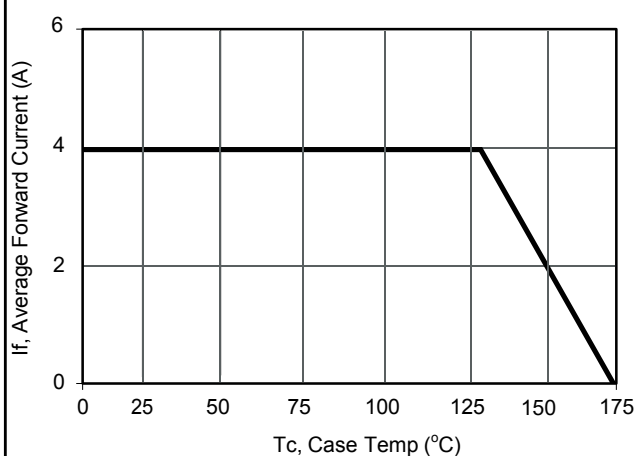
Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

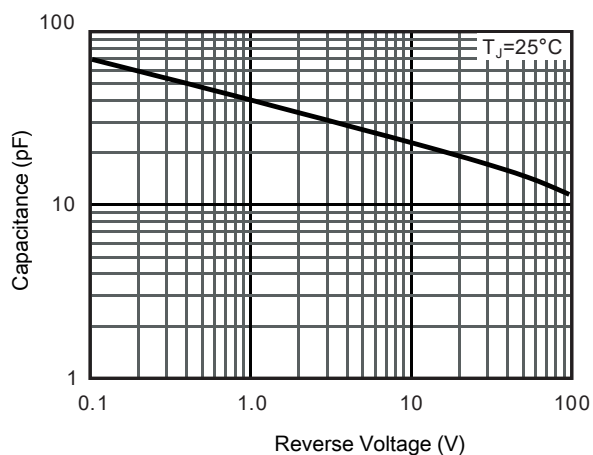
Parameter	Symbols	WRGBP410-S	Units
Maximum Repetitive Peak Reverse Voltage	VRRM	1000	V
Maximum RMS voltage	VRMS	700	V
Maximum DC Blocking Voltage	VDC	1000	V
Average Rectified Output Current	Io	4.0	A
Reverse Recovery Time. IF=0.5A,IR=1A,IRR=0.25A	Trr	10	us
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	IFSM	110	A
I ² t rating for fusing (1ms< t < 10ms)	I ² t	60.5	A ² S
Maximum Forward Voltage at2.0 A	VF	1.0	V
Maximum DC Reverse Current @TA=25 °C at Rated DC Blocking Voltage @TA=125 °C	IR	5 100	μA
Typical Junction Capacitance (Note1)	Cj	40	pF
Operating and Storage Temperature Range	Tj, Tstg	-55 ~ +150	°C

Note: 1. Measured at 1MHz and applied reverse voltage of 4 VDC.

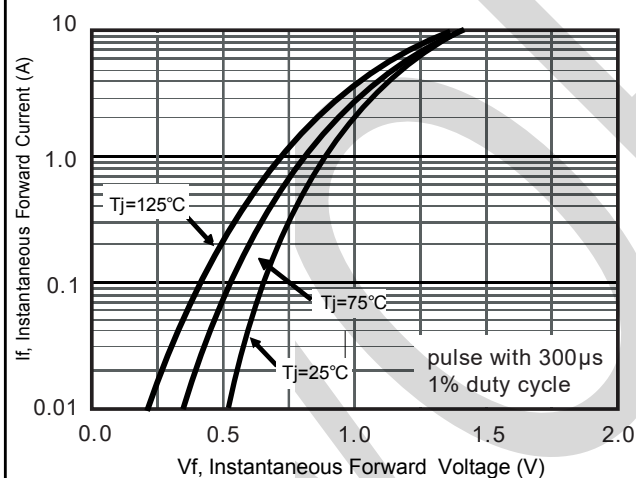
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



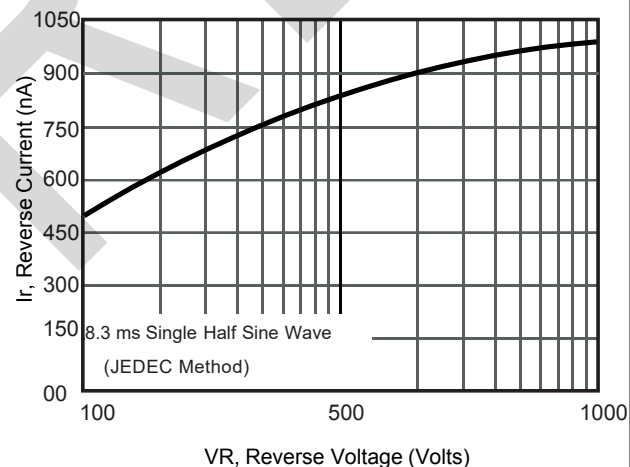
Current Derating, Case



Typical Junction Capacitance

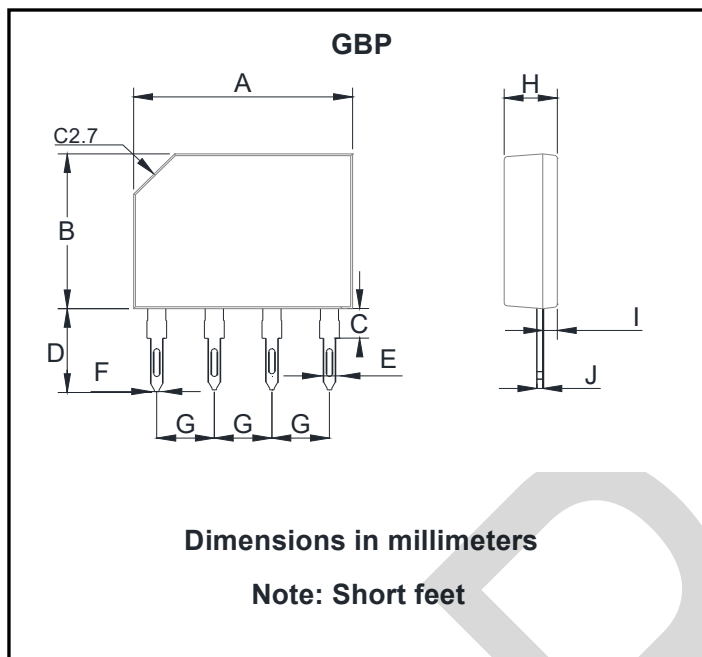


Typical Forward Voltage



Typical Reverse Current

PACKAGE OUTLINE DIMENSIONS



GBP		
Dim	Min	Max
A	14.25	14.75
B	10.10	10.90
C	1.80	2.20
D	5.0	6.2
E	1.22	1.42
F	0.76	0.86
G	3.70	3.90
H	3.35	3.65
I	0.80	1.10
J	0.35	0.55